L Number	Hits	Search Text	DB	Time stamp
17	7657	"alignment mark" or salignment adj mark:	USPAT; EPO; JPO; IBM TDB	12003766103 03:28
21	21294	"shemical mechanical polishing" or CMP	USPAT; BFO; CPO; IBM TDB	2003/6€ 03 09:32
00	33	(("magnetoresistive random access memory" or MRAM) and ("silicon oxide" or SiO or dielectric or insulating) and (Copper or Du) and (Channels or vias or trench or openings))) and ("chemical mechanical polishing" or CMP)	USFAT; EFO; CPO; IEM_TIB	2003/64.03 04:32
20	113	("magnetoresistive random access memory" or MRAM) and (("silicon oxide" or SiO or dielectric or insulating) and (Copper or Cu) and (channels or vias or trench or openings))	USFAT; EFO; JPO; IBM_TIB	2103106.103 19:21
31	112	dielectric or insulating) and (Copper or Cu) and (channels or vias or trench or openings) and ("magnetoresistive random access memory" or MRAM)	USPAT; EFO; JPO; IEM_TIB	2903 06703 11:30
16	568	"magnetoresistive random access memory" or MRAM	, USPAT; - BPO; JPO; - IPM TIB	2 03 06,103 1 :37
34	511	("alignment mark" or (alignment adj mark): and (Copper or Cu) and (channels or vias or trench or openings)	USPĀT; BPO; JPO; IBM TDB	2:03/06/03 10:34
35	144	("magnetoresistive random access memory" or MRAM) and (Copper or Cu) and (channels or vias or trench or openings)	USFĀT; EFC; JPC; IBM TIB	2 03 106,103 1 :39
19	68271	("silicon oxide" or SiO or dielectric or insulating) and (Copper or Cu) and (channels or vias or trench or openings)	USFAT; EFG; JPG; IBM TEB	2 03×06/03 1::52
36		("chemical mechanical polishing" or CMP) and (("silicon oxide" or SiO or dielectric or insulating) and (Copper or Cu) and (channels or vias or trench or openings)) and etch\$3	USFAT; EFI; JPC; IEM_TIB	2:03:06/03 10:53
37	4798	("chemical mechanical polishing" or CMP) and (("silicon oxide" or SiO or dielectric or insulating) and (Copper or Cu) and (channels or vias or trench or openings))	USFAT; EFC; JPC; IEM_TDB	2003/06/03 10:55
38	378	("magnétoresistive random access memory" or MRAM) and (channels or openings or windows or trench or vias or contact)	USFAT; EFC; JPC; IEM TDB	2:03/06/03 1::57
39	46	(("magnetoresistive random access memory" or MRAM) and (channels or openings or windows or trench or vias or contact)) and 43*/\$.sols.	USFĀT; EPO; JPC; IBM_TDB	2003/06/03 10:57